

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td colspan="2" style="text-align: center;"><i>Complete if Known</i></td> </tr> <tr> <td style="width: 50%;">Application Number</td> <td>10/028,643</td> </tr> <tr> <td>Filing Date</td> <td>December 20, 2001</td> </tr> <tr> <td>First Named Inventor</td> <td>Ahn, Kie</td> </tr> <tr> <td>Group Art Unit</td> <td>2814</td> </tr> <tr> <td>Examiner Name</td> <td>Pham, Long</td> </tr> </table>	<i>Complete if Known</i>		Application Number	10/028,643	Filing Date	December 20, 2001	First Named Inventor	Ahn, Kie	Group Art Unit	2814	Examiner Name	Pham, Long
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